



Tile production and test at Hamburg

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CALICE AHCAL & DAQ Meeting – 09.12.2013



- Introduction
- Hamburg university design
- Performance characterization
 - Gain
 - Response to MIP
 - Noise
- Results

Tile design at Hamburg University

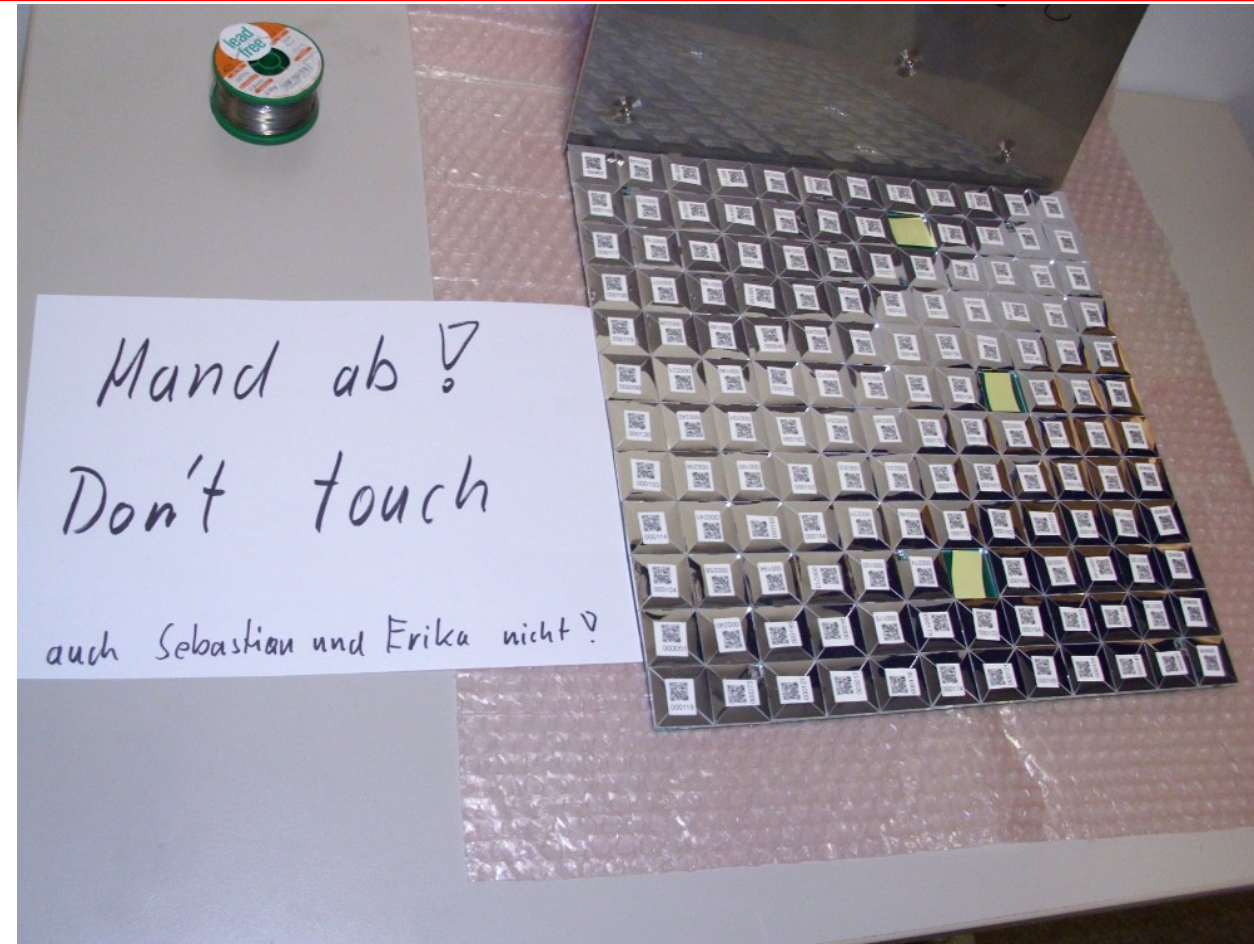
- Individually wrapped in reflector foil
- Without WLS fiber

Aim:

Optimize for mass production

Reduce spread of parameters at V_{OP}

- easier voltage setting
- easier threshold settings



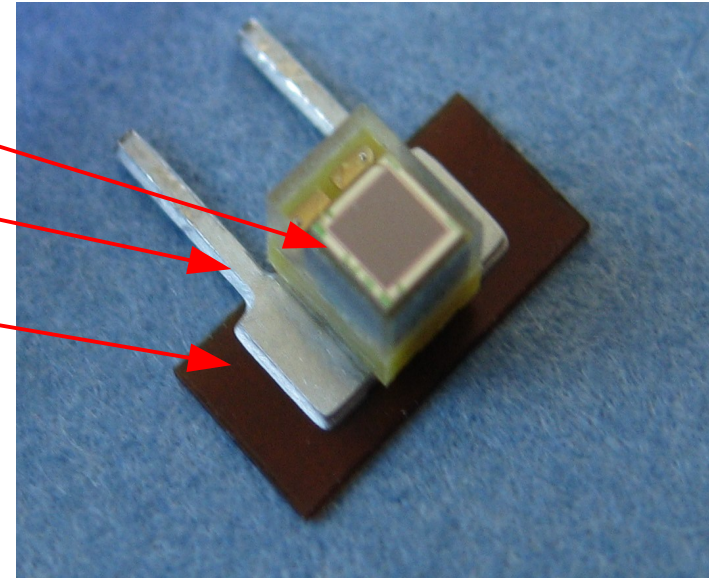
Fully equip 8 HBUs (i.e. ~1200 tiles):

- Two HBUs are operating for the testbeam currently ongoing
- Two more will be ready for beginning of January

UHH tiles: the SiPM

The SiPM:

- 1200 KETEK PM1125 SMD mounted
- Peak sensitivity at $\lambda = 420 \text{ nm}$
- SMD mounting soldered on copper pins
- Pins glued to Kapton foil



Constraints from electronics:

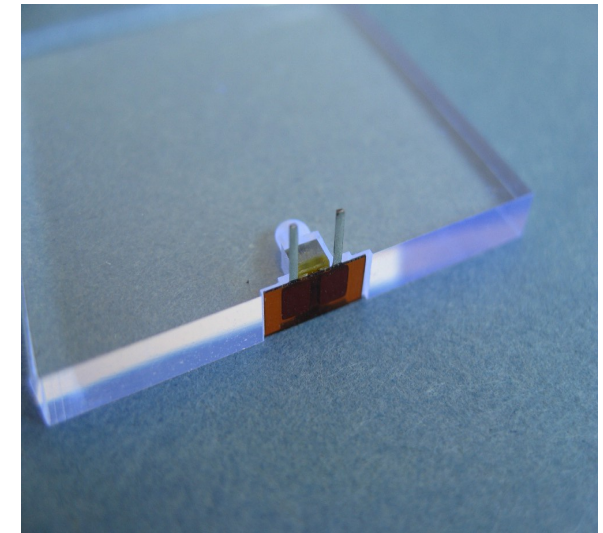
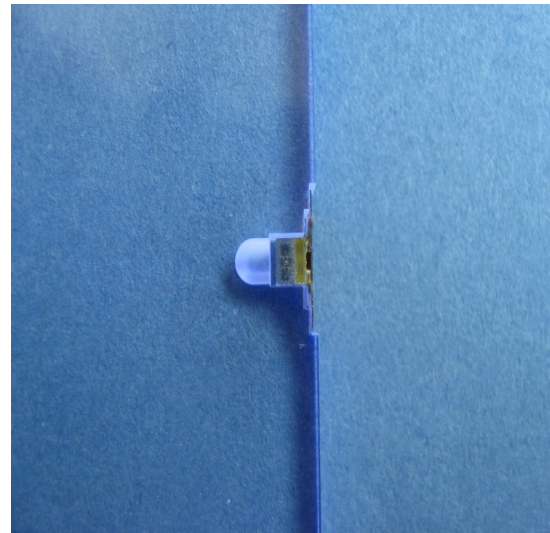
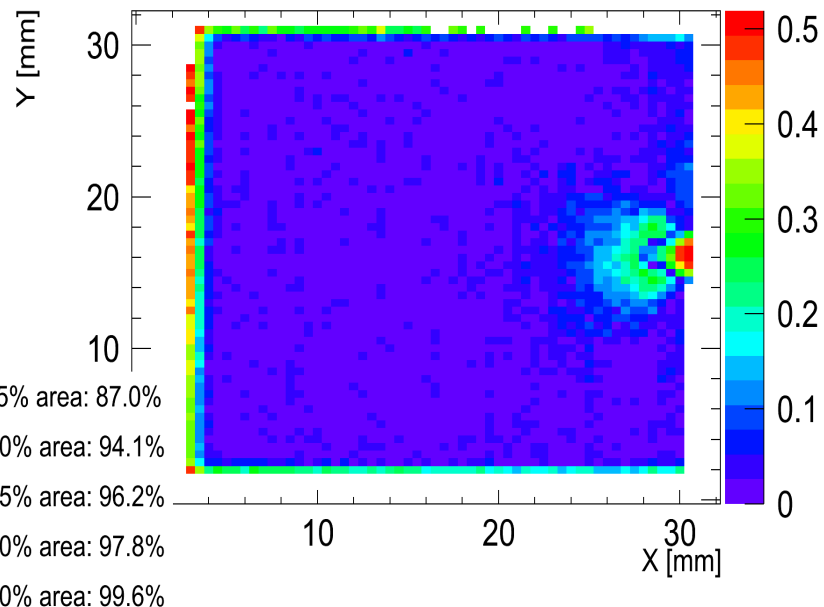
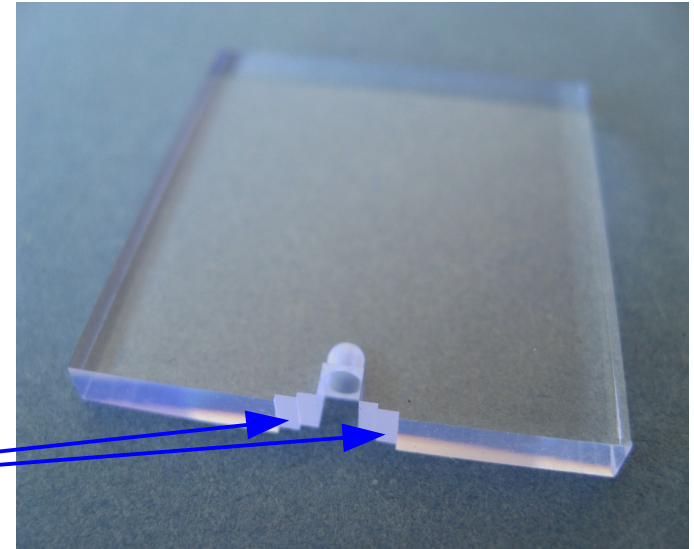
- Gain at $V_{OP} > 6 \times 10^5$ to allow gain adjustment with pre-amplifiers
- Spread in $V_{OP} < 2 \text{ V}$

	Gain [e-]	DCR	Cross talk	dV_{BD}/dT	N of pixels
KETEK PM1125	0.7×10^6	0.2 Mcps	~ 5%	~15 mV/K	2300
CPTA	$(0.7-2) \times 10^6$	1 Mcps	~ 1%	20 mV/K	798

UHH tiles: the scintillator

The tile:

- Bicron BC-400 Polyvinyltoluene
- Peak emission: $\lambda = 423 \text{ nm}$
- 0.9 ns rise time, 2.7 ns pulse width (FWHM)
- **Machined** instead of molded:
 - Improve accuracy on dimensions ($\sim 10 \mu\text{m}$)
- **No WLS fiber:**
 - Machined coupling to match SiPM
 - Kapton support glued to plastic tile
 - “cathedral” drill in front of the SiPM to improve uniformity

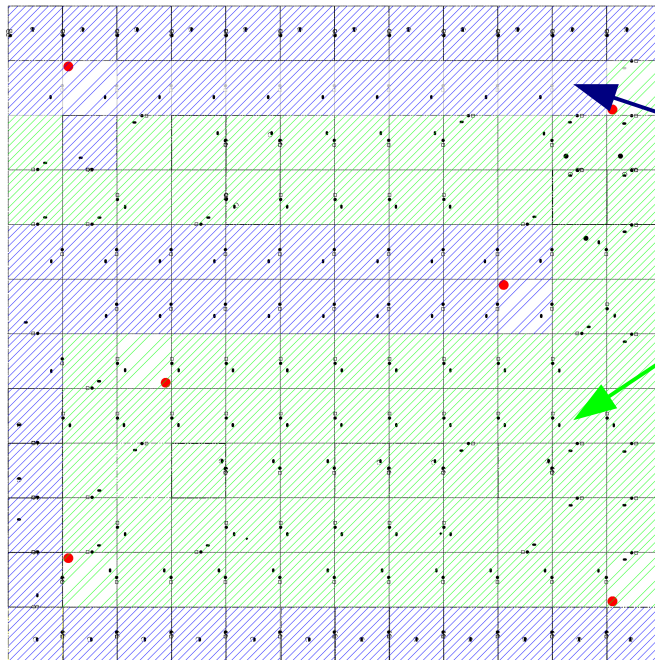


UHH tiles: wrapping

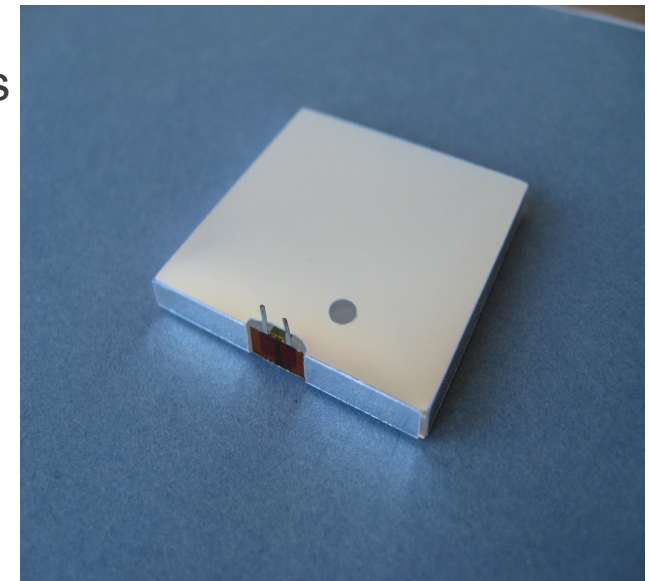
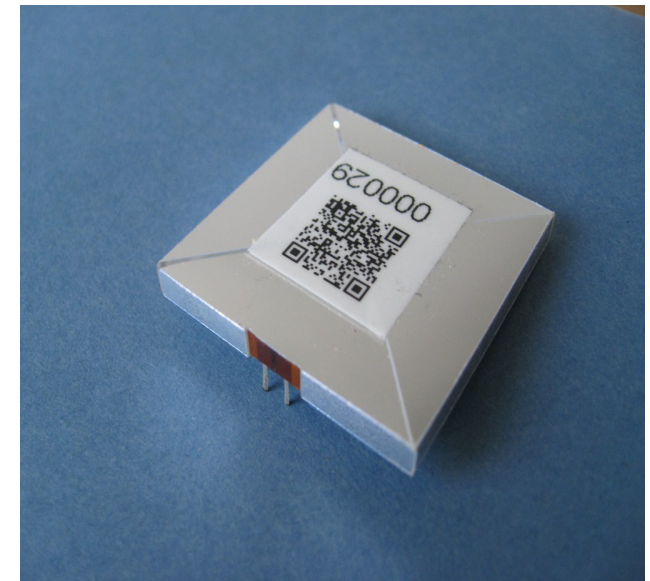
Wrapping:

- Tiles are wrapped with 3M Vikuiti reflector foil
 - 65 μm thick
 - 98% reflectivity
- Foil cut with laser cutter;
 - Hole for SiPM monitoring via LED on the HBU
 - Cut for two different hole positions
- **mechanically wrapped** around the tile;
- Fixed with sticker with QR code for unique identification

map of LED positions on HBU



75% of LED positions

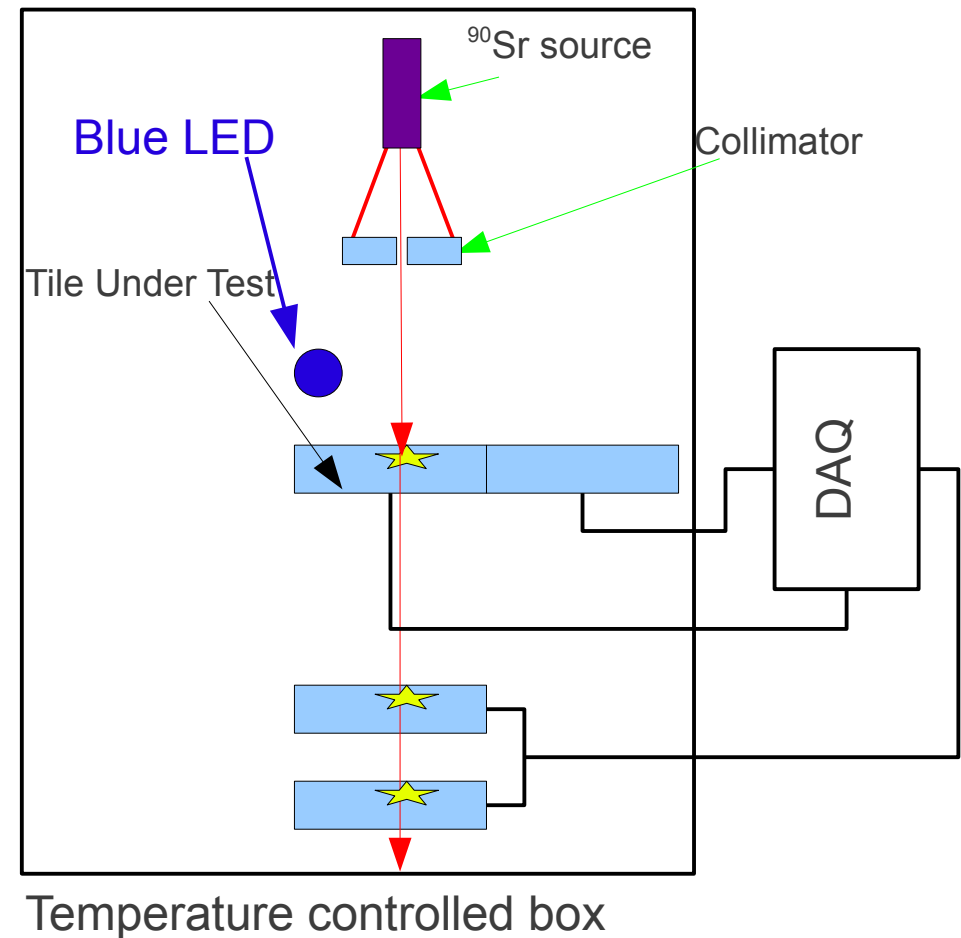
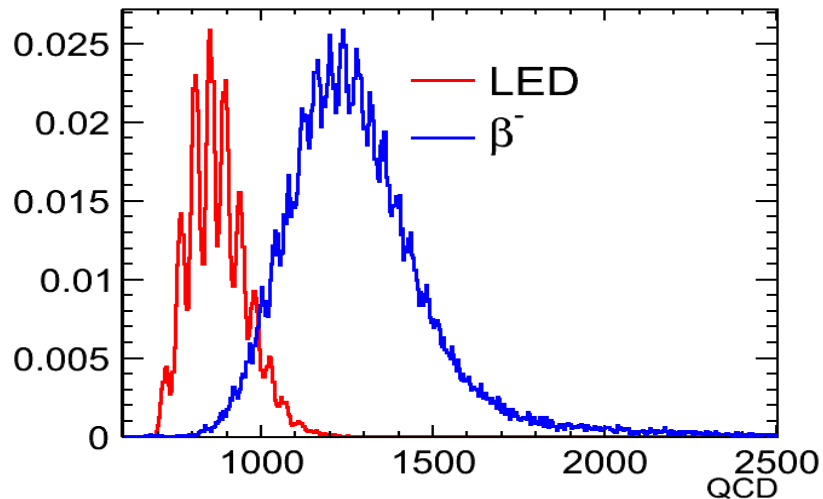


Tile performance characterization



Measure:

- SiPM parameters:
 - Gain
 - DCR
 - inter pixel cross talk
 - temperature dependence
- Response to one MIP (in n. of pixels);
- Light cross talk between tiles

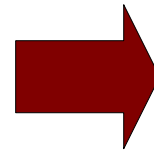
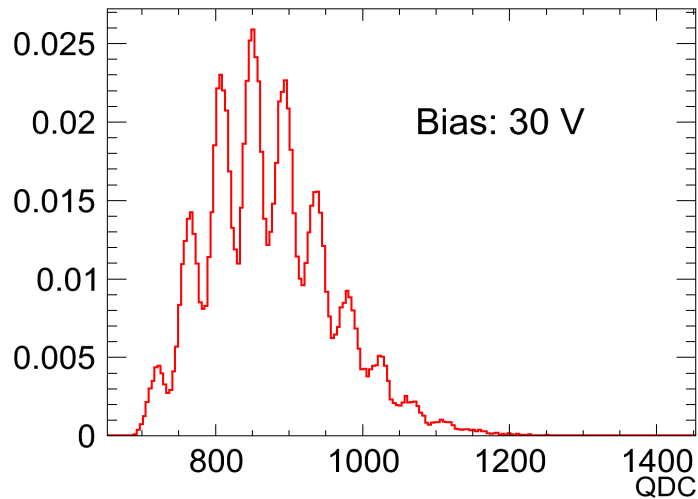


- Small batch (~100 tiles and counting) characterized at Hamburg University;
- Used as a reference for mass calibration set-up being commissioned at KIP Heidelberg

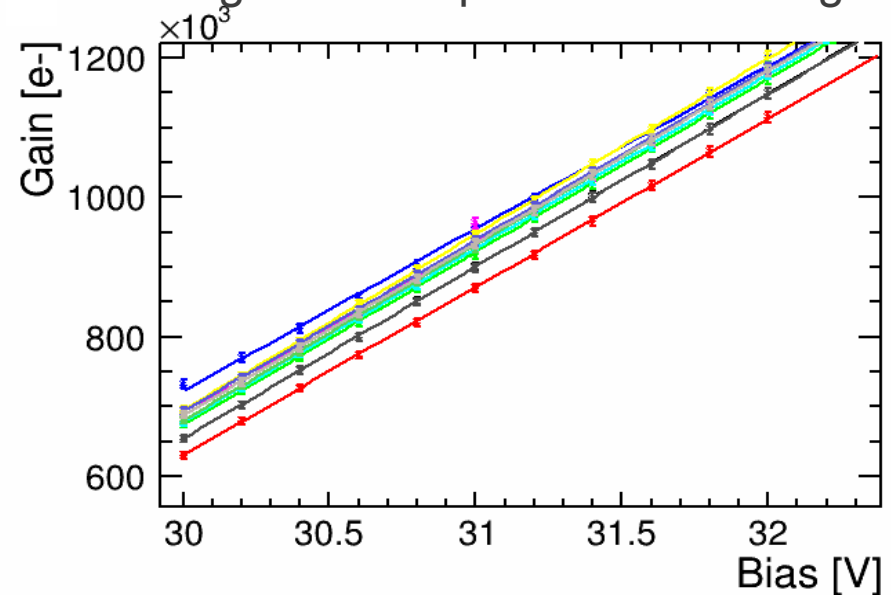
SiPM characterization: Gain



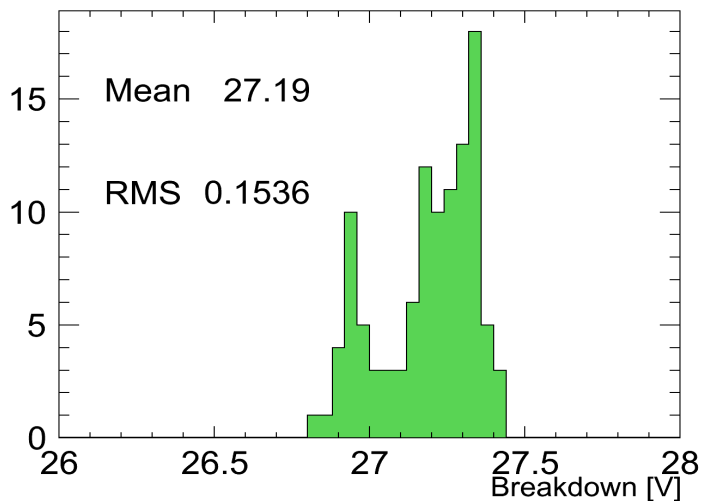
SiPM spectrum:
Gain from multi-peak fit



Voltage and temperature scan of gain



Breakdown



- **Min-to-max: 0.6 V**
- Two batches of SiPMs clearly visible

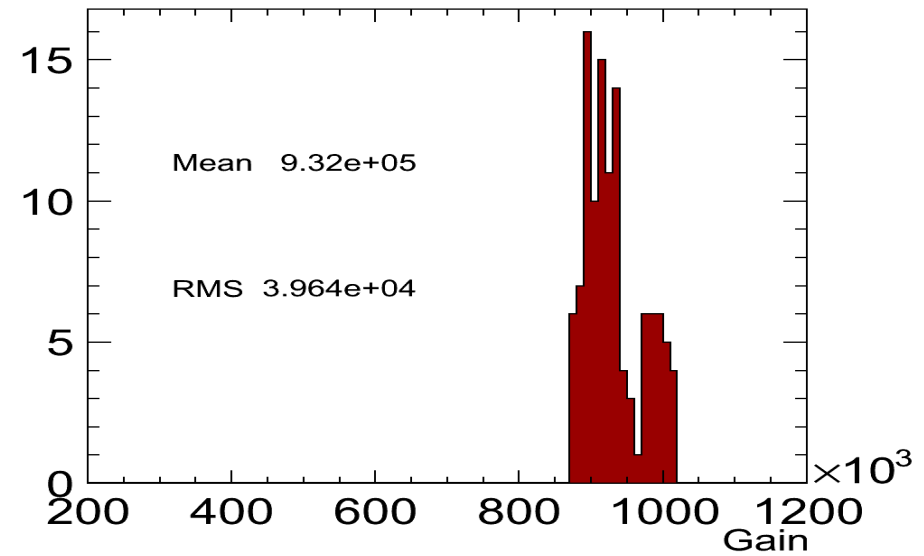
SiPM characterization: Gain



Set all the SiPMs at same V_{OP} (+31 V):

- Gain spread of 4%
- Min-to-max: 1.4×10^5
- Two SiPMs batches still visible

Gain fixV



SiPM characterization: Gain



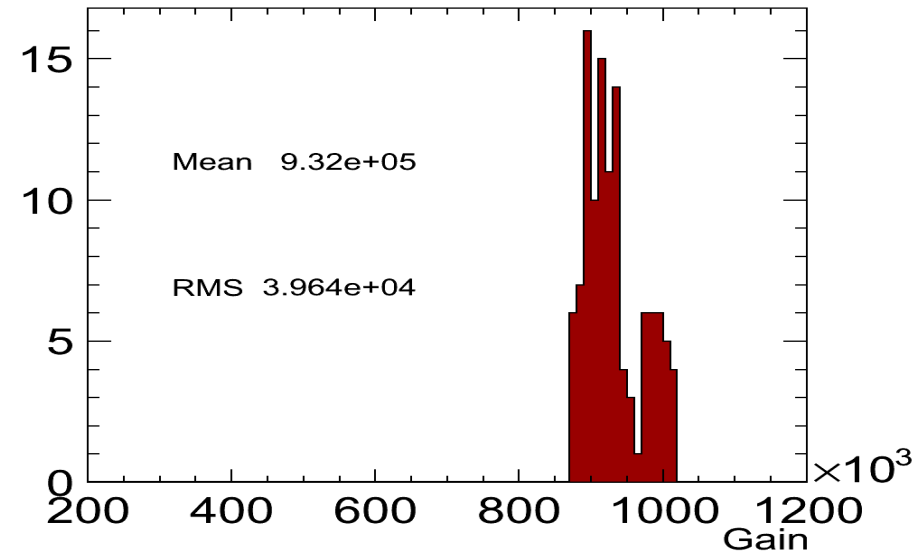
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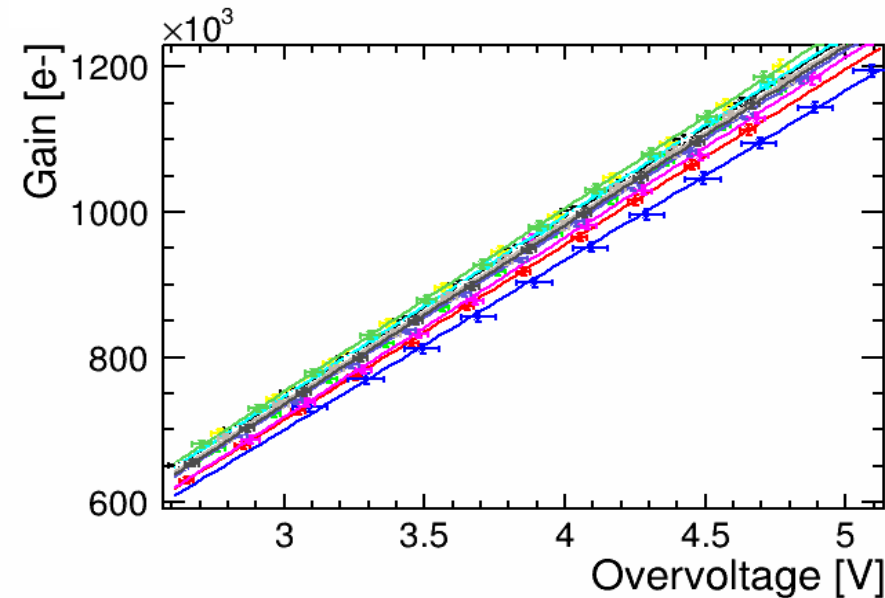
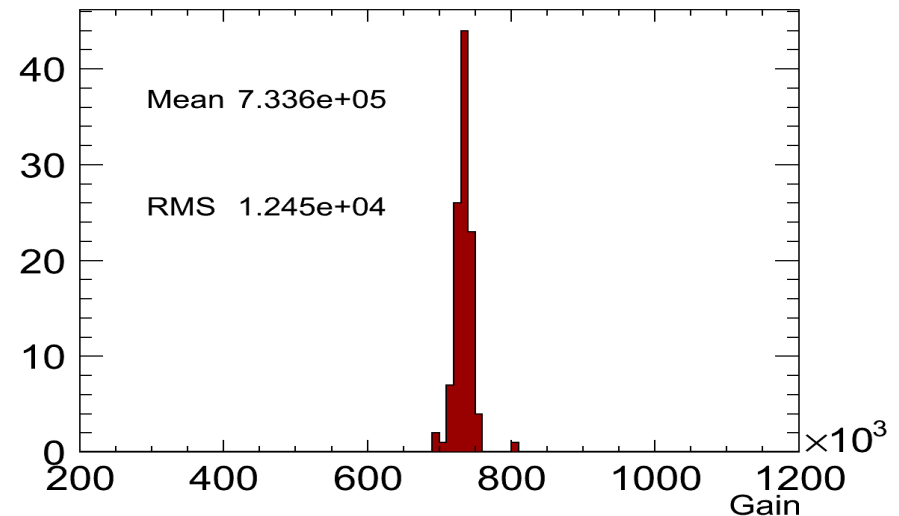
Set all the SiPMs at same Excess Bias (+3 V):

- Gain spread of 2%
- Min-to-max: 1.1×10^5
- Two SiPMs batches disappear

Gain fixV



Gain 30V



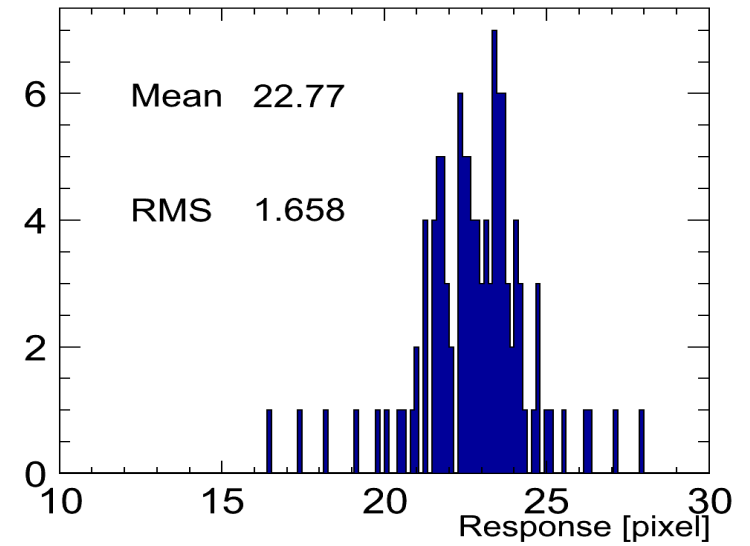
Tile characterization: Response



Set all the SiPMs at same V_{OP} (+31 V):

- Response spread of 7.5%
- Min-to-max: 11 pixels

Response fixV



Tile characterization: Response

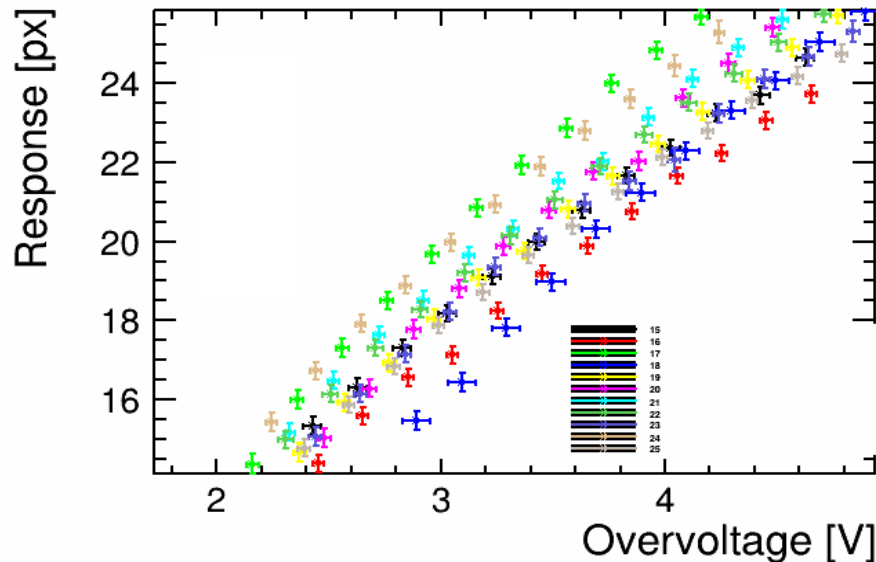


Set all the SiPMs at same V_{OP} (+31 V):

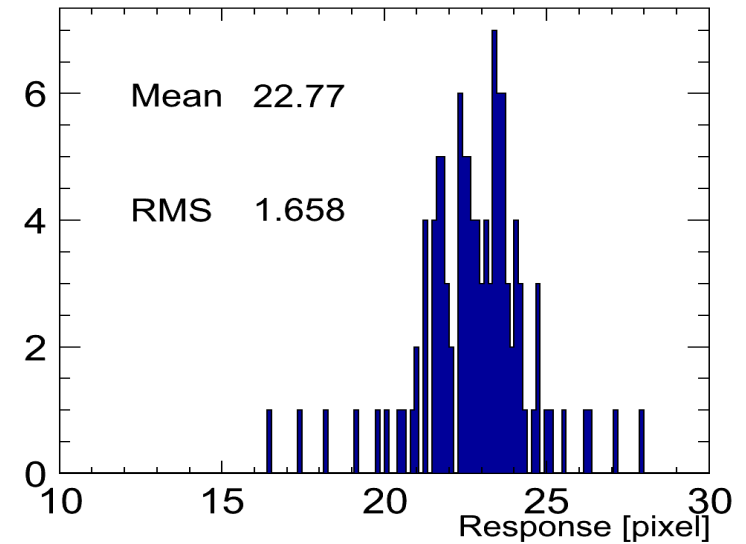
- Response spread of 7.2%
- Min-to-max: 12 pixels

Set all the SiPMs at same Excess Bias (+3 V):

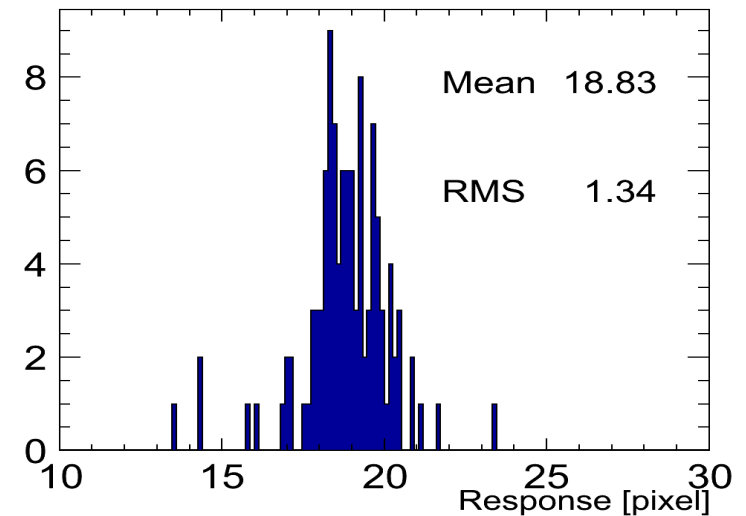
- Response spread of 7.1%
- Min-to-max: 10 pixels



Response fixV



Response 30V



Tile characterization: Noise



Set all the SiPMs at same V_{OP} (+31 V):

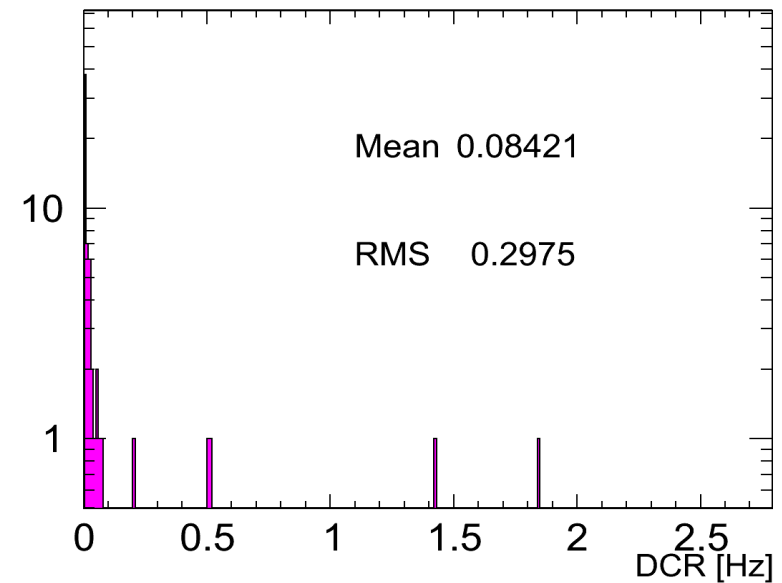
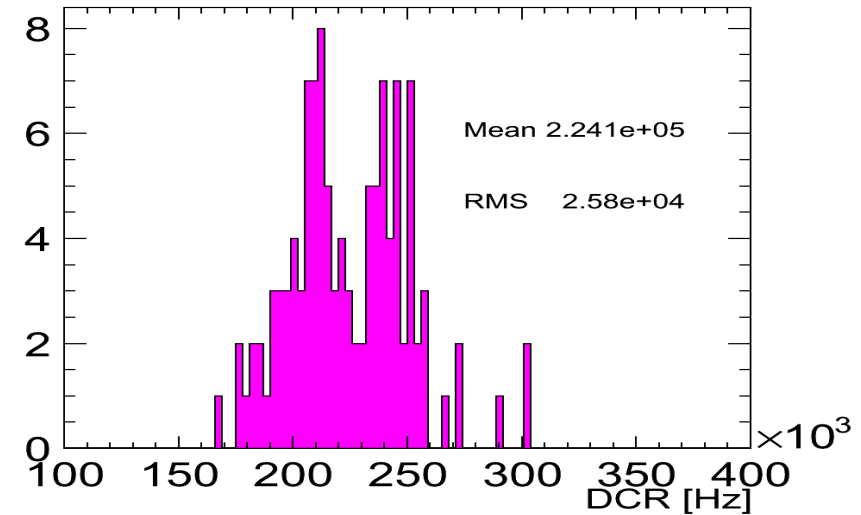
DCR at 0.5 p.e. Threshold

- Mean: 224 kHz
- Spread: 10%

DCR at 0.2 MIP Threshold

- Mean \sim 0.1 Hz

DCR fixV



SiPM noise is negligible

- Single channel (tile) design optimized for mass production finalized at Hamburg University
- Mass production started
- Characterization of SiPMs show small parameter spread:
 - 600 mV min-to-max spread for breakdown voltage
 - ~ 15 mV/K temperature dependence
 - Possible operation at same threshold and same V_{OP}
- If V_{OP} is set individually:
 - 2% spread on gain
 - 7% spread on response to MIP
- Noise due to SiPM DCR is negligible for thresholds > 0.2 MIP
- Outlook:
 - Mass characterization ongoing
 - Cross check results
 - Install tiles on HBUs and test performances in beam environment

Backup Slides



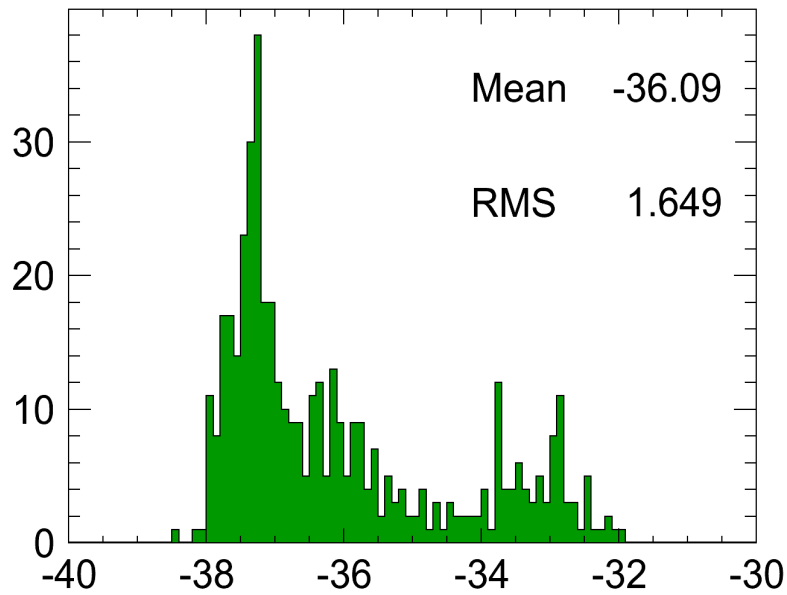
Universität Hamburg

DER FORSCHUNG | DER LEHRE | DER BILDUNG

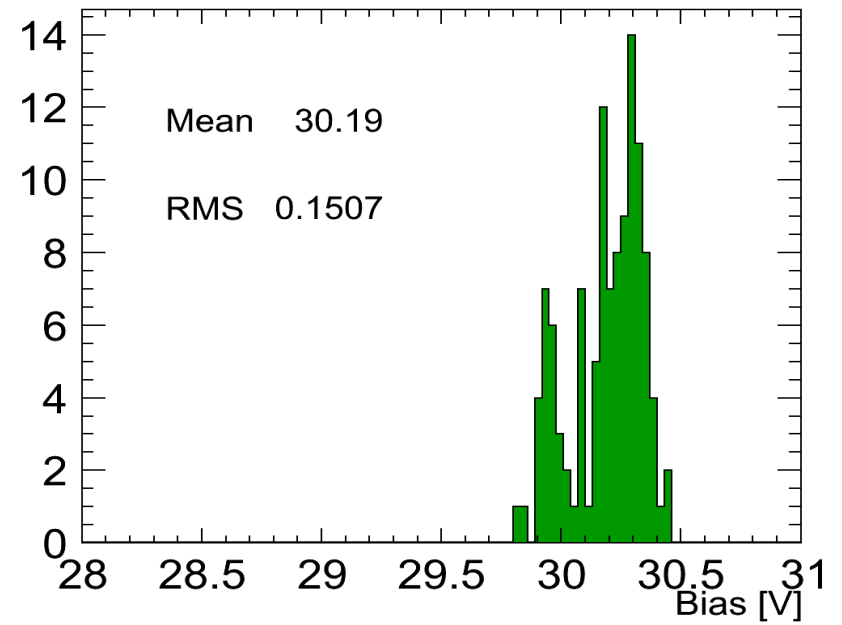
ITEP Tiles: Operating Voltage



ITEP_VOP



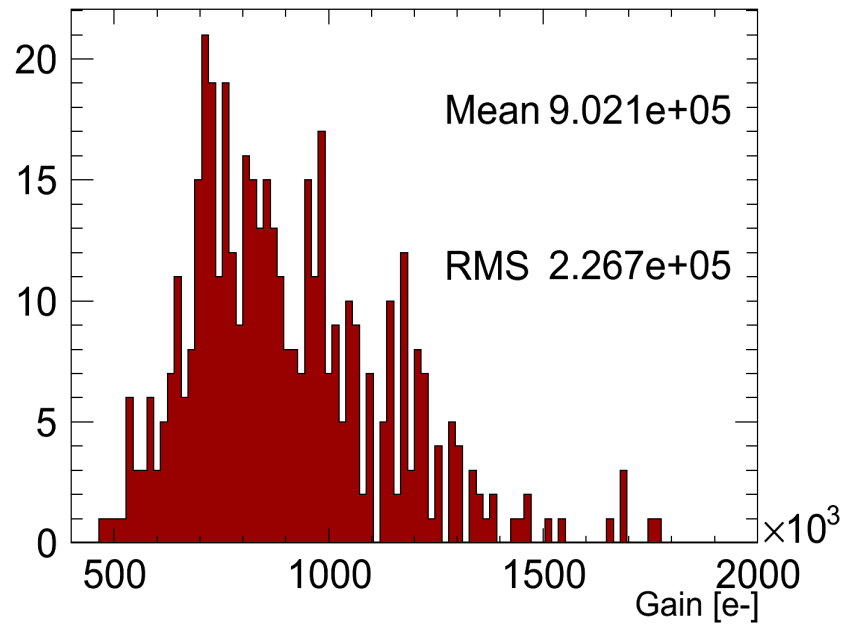
OpVOIt



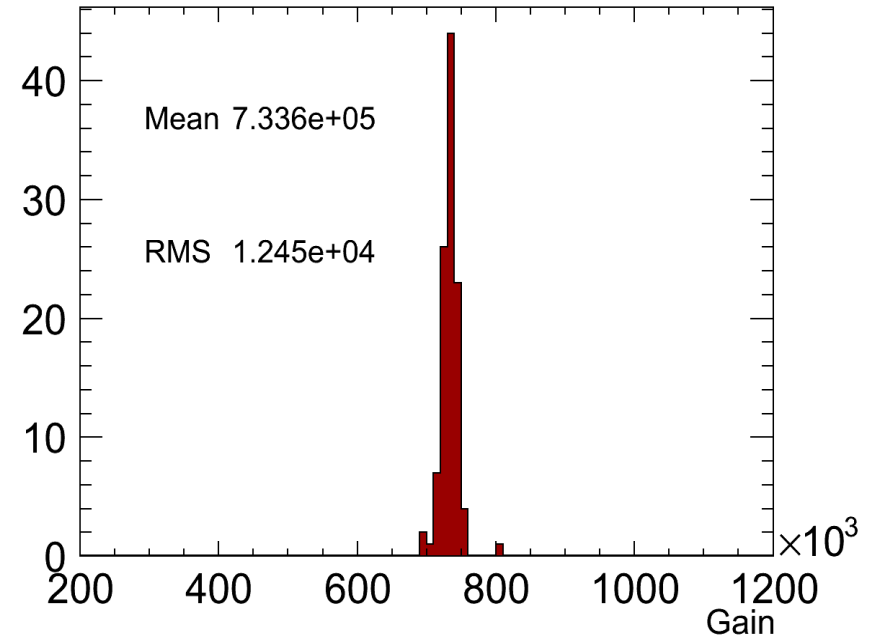
ITEP Tiles: Gain



ITEP_GAIN



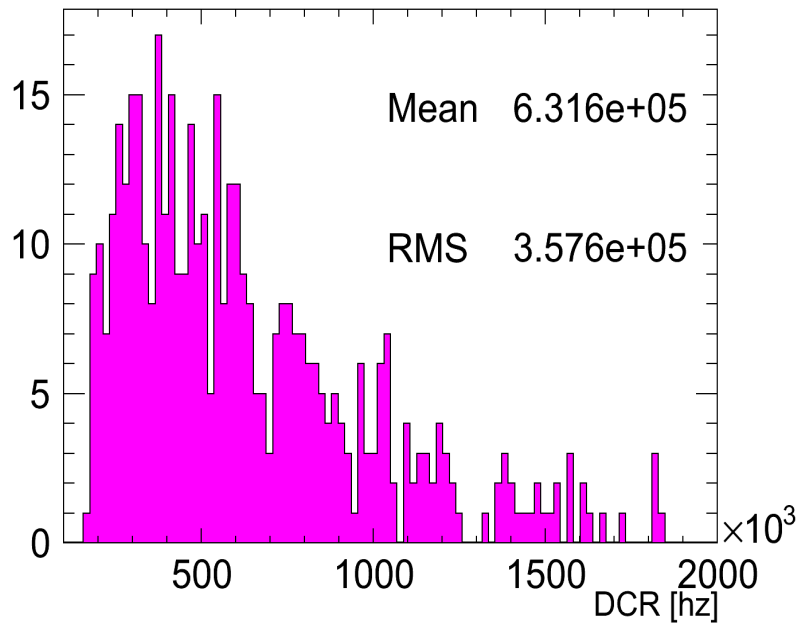
Gain 30V



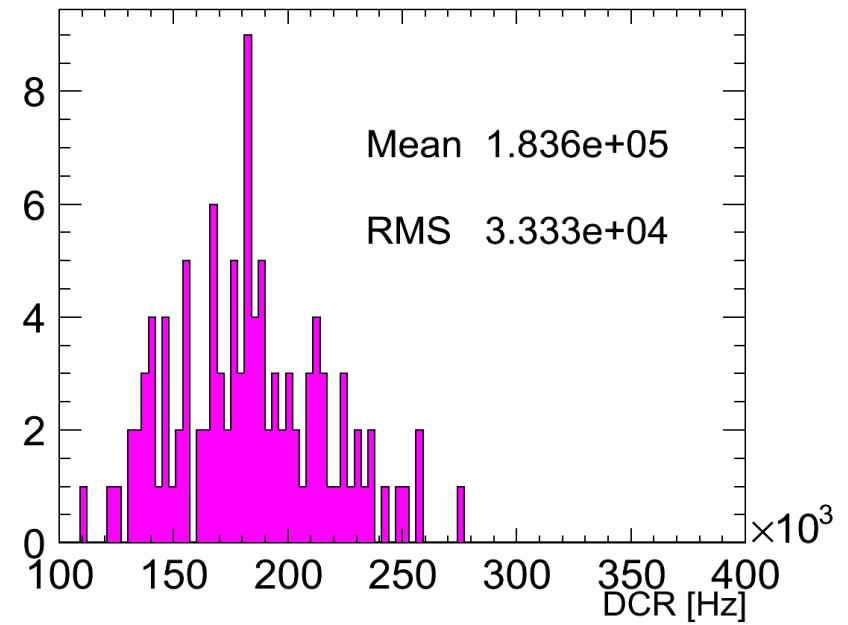
ITEP Tiles: DCR



ITEP_NOISE



DCR 30V



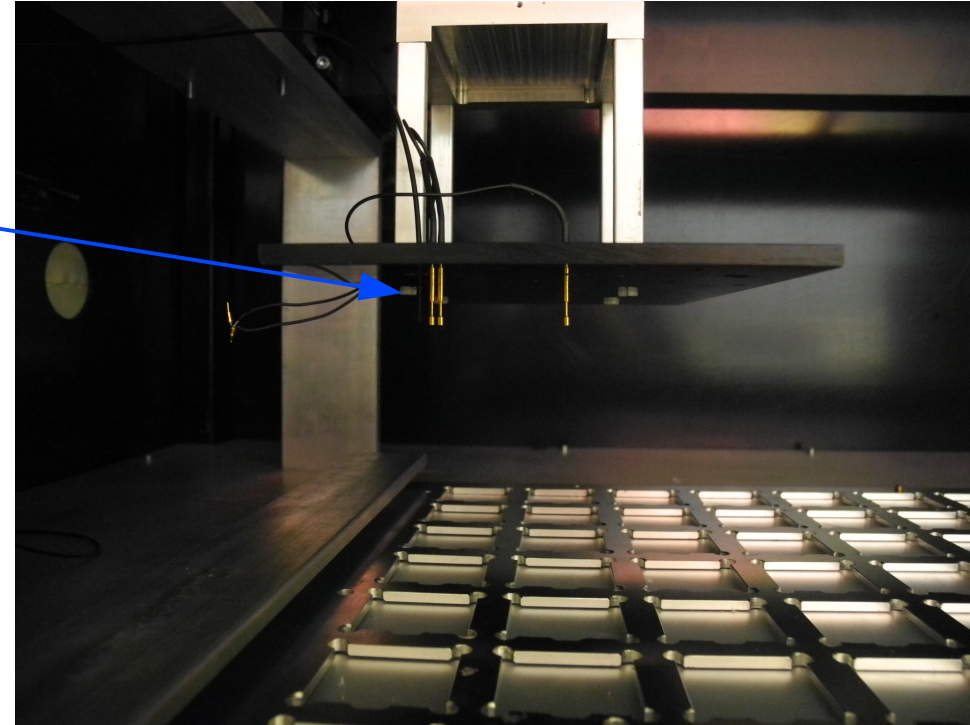
Use **UV laser** on tiles instead of electrons

Calibration procedure

Previously characterized tile:

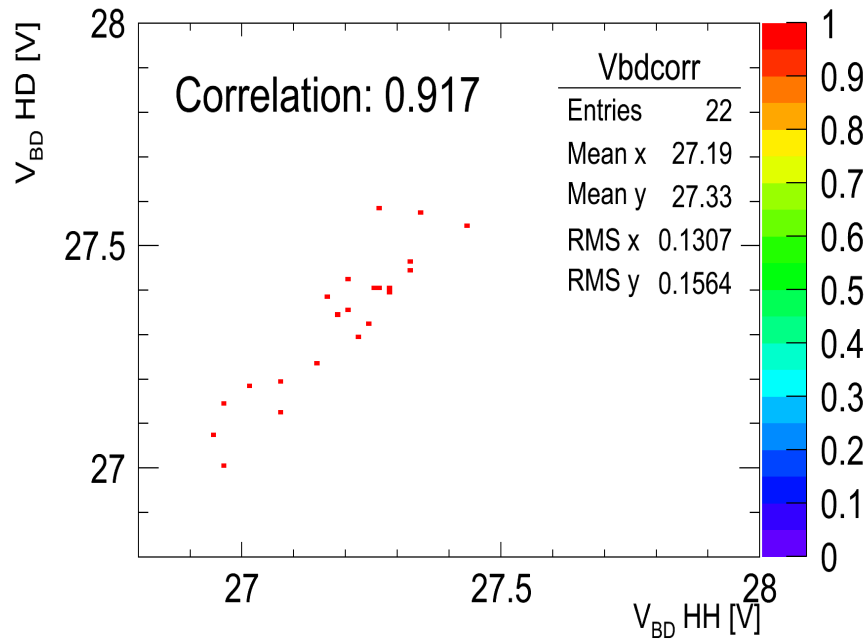
- Set tile voltage
- Adjust laser intensity until:

$$\text{Response(Laser)[pixel]} = \text{Response(MIP)[pixel]}$$



Perform voltage scan of tile response

144 tiles had been shipped to Heidelberg (of which 25 already characterized)



KIP result and UHH result strongly correlated

- The two values present an offset
- Origin still to investigated

